

NPN SILICON HI FREQUENCY TRANSISTOR

DESCRIPTION:

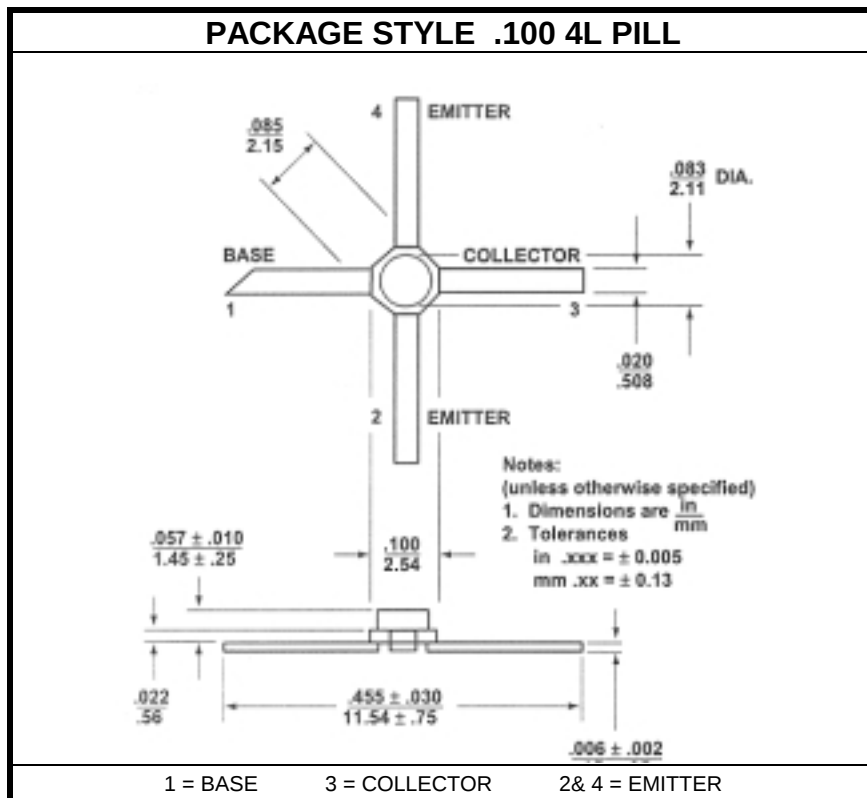
The **ASI NE21935** is Designed for general purpose and small signal amplifier and oscillator applications up to 6.0 GHz.

FEATURES INCLUDE:

- High frequency 8.0 GH
- Low noise, 1 dB at 0.5 GHz.

MAXIMUM RATINGS:

I_C	80 mA
V_{CBO}	20 V
V_{CEO}	10 V
V_{EBO}	1.5 V
P_{DISS}	580 mW @ $T_A = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+200^\circ C$
θ_{JC}	80 $^\circ C/W$



CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
I_{CBO}	$V_{CB} = 8.0 V$				1.0	μA
I_{EBO}	$V_{EB} = 1.0 V$				1.0	μA
h_{FE}	$V_{CE} = 8.0 V$	$I_C = 20 mA$	30	100	300	---
C_{CB}	$V_{CB} = 8.0 V$	$f = 1.0 MHz$		0.4	1.0	pF
f_T	$V_{CE} = 8.0 V$	$I_C = 20 mA$		8.0		GHz
$ S_{21E} $	$V_{CE} = 8.0 V$	$I_C = 20 mA$		15.5		dB
		$f = 2.0 GHz$	8.0	9.0		